

Photoresponse spectrum in differently irradiated and annealed Si

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The experimental results of photoconductivity response spectra in different samples (irradiation and low temperature annealing) are summarized and a set of optical activation energies is determined. The photoresponse was measured by instantaneous excitation and by excitation by 40 fs pulse generated by the tunable laser. The photoconductivity origin is analyzed taking into account the deep levels in the clusters and in the bulk. The peculiarities of the persistent photoconductivity are discussed.

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